

Advanced Chemistry-Independent, Level 2 Battery Charger with Input Current Limiting

General Description

The MAX1645B is a high-efficiency battery charger capable of charging batteries of any chemistry type. It uses the Intel System Management Bus (SMBus™) to control voltage and current-charge outputs.

When charging lithium-ion (Li+) batteries, the MAX1645B automatically transitions from regulating current to regulating voltage. The MAX1645B can also limit line input current so as not to exceed a predetermined current drawn from the DC source. A 175s charge safety timer prevents "runaway charging" should the MAX1645B stop receiving charging voltage/current commands.

The MAX1645B employs a next-generation synchronous buck control circuitry that lowers the minimum input-to-output voltage drop by allowing the duty cycle to exceed 99%. The MAX1645B can easily charge one to four series Li+ cells.

Applications

Notebook Computers Point-of-Sale Terminals Personal Digital Assistants

DCIN 1

LDO 2

CLS 3 REF 4

CCS 5

CCI 6

CCV 7

GND 8

BATT 9

DAC 10

V_{DD} 11

THM 12

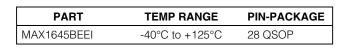
SCL 13

SDA 14

_Features

- Input Current Limiting
- 175s Charge Safety Timeout
- 128mA Wake-Up Charge
- Charges Any Chemistry Battery: Li+, NiCd, NiMH, Lead Acid, etc.
- ♦ Intel SMBus 2-Wire Serial Interface
- Compliant with Level 2 Smart Battery Charger Spec Rev 1.0
- ♦ +8V to +28V Input Voltage Range
- Up to 18.4V Battery Voltage
- 11-Bit Battery Voltage Setting
- ♦ ±0.8% Output Voltage Accuracy with Internal Reference
- ♦ 3A (max) Battery Charge Current
- ♦ 6-Bit Charge-Current Setting
- 99.99% (max) Duty Cycle for Low-Dropout Operation
- Load/Source Switchover Drivers
- >97% Efficiency

_Ordering Information





SMBus is a trademark of Intel Corp.

TOP VIEW

Maxim Integrated Products 1

For pricing, delivery, and ordering information, please contact Maxim/Dallas Direct! at 1-888-629-4642, or visit Maxim's website at www.maxim-ic.com.

Pin Configuration

28 CVS 27 PDS

26 CSSP

25 CSSN

24 BST

23 DHI

22 LX

21 DLOV

20 DL0

19 PGND 18 CSIP

17 CSIN 16 PDL

15 INT

MIXIM

MAX1645B

QSOP

ABSOLUTE MAXIMUM RATINGS

| DCIN, CVS, CSSP, CSSN, LX to GND. CSSP to CSSN, CSIP to CSIN | |
|---|--|
| PDS, PDL to GND | |
| BST to LX | -0.3V to +6V |
| DHI to LX | 0.3V to (V _{BST} + 0.3V) |
| CSIP, CSIN, BATT to GND | |
| LDO to GND0.3V to (lov | ver of 6V or V _{DCIN} + 0.3V) |
| DLO to GND | 0.3V to (V _{DLOV} + 0.3V) |
| REF, DAC, CCV, CCI, CCS, CLS to GNI | D0.3V to $(V_{LDO} + 0.3V)$ |

| V _{DD} , SCL, SDA, INT, DLOV to GND0.3 THM to GND0.3 | |
|--|---------------|
| PGND to GND | 0.3V to +0.3V |
| LDO Continuous Current | 50mA |
| Continuous Power Dissipation ($T_A = +70^{\circ}C$) | |
| 28-Pin QSOP (derate 10.8mW/°C above +7 | 0°C)860mW |
| Operating Temperature Range | 40°C to +85°C |
| Storage Temperature Range | |
| Lead Temperature (soldering, 10s) | +300°C |

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

(Circuit of Figure 1, V_{DD} = +3.3V, V_{BATT} = +16.8V, V_{DCIN} = +18V, **T_A** = 0°C to +85°C, unless otherwise noted. Typical values are at T_A = +25°C.)

| PARAMETER | SYMBOL | CONDIT | MIN | ТҮР | MAX | UNITS | |
|--|----------------------|---|---------------------------|-------|-------|-------|----|
| GENERAL SPECIFICATIONS | | · | | | | | |
| DCIN Typical Operating Range | VDCIN | | | 8 | | 28 | V |
| DCIN Supply Current | IDCIN | $8V < V_{DCIN} < 28V$ | | | 1.7 | 6 | mA |
| DCIN Supply Current Charging Inhibited | | $8V < V_{DCIN} < 28V$ | | 0.7 | 2 | mA | |
| DCIN Undervoltage Threshold | | When AC_PRESENT | DCIN rising | | 7.5 | 7.85 | v |
| DCIN Ondervoltage Threshold | | switches | DCIN falling | 7 | 7.4 | | V |
| LDO Output Voltage | VLDO | $8V < V_{DCIN} < 28V, 0 <$ | I _{LDO} < 15mA | 5.15 | 5.4 | 5.65 | V |
| V _{DD} Input Voltage Range | | $8V < V_{DCIN} < 28V$ (Note | e 1) | 2.80 | | 5.65 | V |
| V _{DD} Undervoltage Threshold | | When the SMB | V _{DD} rising | | 2.55 | 2.8 | V |
| VDD Ondervoltage Threshold | | responds to commands | V _{DD} falling | 2.1 | 2.5 | | v |
| V _{DD} Quiescent Current | IDD | $0 < V_{DCIN} < 6V, V_{DD} = V_{SDA} = 5V$ | | 80 | 150 | μA | |
| REF Output Voltage | VREF | 0 < I _{REF} < 200µA | | 4.066 | 4.096 | 4.126 | V |
| BATT Undervoltage Threshold | | When ICHARGE drops to | o 128mA (Note 2) | 2.4 | | 2.8 | V |
| PDS Charging Source Switch Turn-Off Threshold | V _{PDS-OFF} | V _{CVS} referred to V _{BATT} , V _{CVS} falling | | 50 | 100 | 150 | mV |
| PDS Charging Source Switch Threshold Hysteresis | VPDS-HYS | V _{CVS} referred to V _{BATT} | | 100 | 200 | 300 | mV |
| PDS Output Low Voltage, PDS Below CSSP | | IPDS = 0 | | 8 | 10 | 12 | V |
| PDS Turn-On Current | | PDS = CSSP | | 100 | 150 | 300 | μA |
| PDS Turn-Off Current | | VPDS = VCSSP - 2V, VDC | CIN = 16V | 10 | 50 | | mA |
| PDL Load Switch Turn-Off Threshold | VPDL-OFF | V_{CVS} referred to V_{BATT} , | , V _{CVS} rising | -150 | -100 | -50 | mV |

ELECTRICAL CHARACTERISTICS (continued)

(Circuit of Figure 1, V_{DD} = +3.3V, V_{BATT} = +16.8V, V_{DCIN} = +18V, **T_A** = 0°C to +85°C, unless otherwise noted. Typical values are at T_A = +25°C.)

| PARAMETER | SYMBOL | CON | DITIONS | MIN | ТҮР | MAX | UNITS | | |
|--|----------|--|--|--------|--------|--------|-------|--|--|
| PDL Load Switch Threshold Hysteresis | VPDL-HYS | V_{CVS} referred to V_{BA} | ATT | 100 | 200 | 300 | mV | | |
| PDL Turn-Off Current | | V _{CSSN} - V _{PDL} = 1V | | 6 | 12 | | mA | | |
| PDL Turn-On Resistance | | PDL to GND | | 50 | 100 | 150 | kΩ | | |
| CVS Input Bias Current | | $V_{CVS} = 28V$ | | | 6 | 20 | μA | | |
| | | ChargingVoltage() = | = 0x41A0 | 16.666 | 16.8 | 16.934 | | | |
| | 1/0 | ChargingVoltage() = | = 0x3130 | 12.492 | 12.592 | 12.692 | M | | |
| BATT Full-Charge Voltage | VO | ChargingVoltage() = | 8.333 | 8.4 | 8.467 | V | | | |
| | | ChargingVoltage() = | = 0x1060 | 4.150 | 4.192 | 4.234 | | | |
| BATT Charge Current-Sense | | | ChargingCurrent() = 0x0BC0 | 139.9 | 150.4 | 160.9 | | | |
| Voltage | 10 | VCSIP - VCSIN | ChargingCurrent() = 0x0080 | 3.08 | 6.4 | 9.72 | mV | | |
| DCIN Source Current-Limit | | | V _{CLS} = 4.096V | 188.6 | 204.8 | 221.0 | | | |
| Sense Voltage | | VCSSP - VCSSN | V _{CLS} = 2.048V | 91.3 | 102.4 | 113.5 | mV | | |
| BATT Undervoltage Charge Current-Sense VoltageVCSIP - VCSINVBATT = 1V | | | 3.08 | 6.4 | 9.72 | mV | | | |
| Inductor Peak Current Limit | | V _{CSIP} - V _{CSIN} | | 250 | 300 | 350 | mV | | |
| BATT/CSIP/CSIN Input Voltage Range | | VCSIP - VCSIN | | 0 | | 20 | V | | |
| Total BATT Input Bias Current | | Total of I _{BATT} , I _{CSIP} , V _{BATT} = 0 to 20V | and I _{CSIN} ; | -700 | | +700 | μA | | |
| Total BATT Quiescent Current | | Total of I _{BATT} , I _{CSIP} , V _{BATT} = 0 to 20V, cl | | -100 | | +100 | μA | | |
| Total BATT Standby Current | | Total of I_{BATT} , I_{CSIP} , $V_{BATT} = 0$ to 20V, V_{I} | | -5 | | +5 | μA | | |
| CSSP Input Bias Current | | $V_{CSSP} = V_{CSSN} = V_{I}$ | DCIN = 0 to 28V | -100 | 540 | +1000 | μA | | |
| CSSN Input Bias Current | | $V_{CSSP} = C_{CSSN} = V$ | DCIN = 0 to 28V | -100 | 35 | +100 | μA | | |
| CSSP/CSSN Quiescent Current | | $V_{CSSP} = V_{CSSN} = 28$ | BV, V _{DCIN} = 0 | -1 | | +1 | μA | | |
| Battery Voltage-Error Amp DC Gain | | From BATT to CCV | | 200 | 500 | | V/V | | |
| CLS Input Bias Current | | $V_{CLS} = V_{REF}/2$ to V_{REF} | REF | -1 | +0.05 | +1 | μA | | |
| Battery Voltage-Error Amp Transconductance | | From BATT to CCV, $0x41A0$, $V_{BATT} = 16$ | 0.111 | 0.222 | 0.444 | µA/mV | | | |
| Battery Current-Error Amp Transconductance | | From CSIP/CSIN to $($ = 0x0BC0, V _{CSIP} - V | 0.5 | 1 | 2.0 | µA/mV | | | |
| Input Current-Error Amp Transconductance | | From CSSP/CSSN to $V_{CSSP} - V_{CSSN} = 10$ | o CCS, V _{CLS} = 2.048V, 2.4mV | 0.5 | 1 | 2.0 | µA/mV | | |
| CCV/CCI/CCS Clamp Voltage | | VCCV = VCCI = VCCS | s = 0.25V to 2V (Note 3) | 150 | 300 | 600 | mV | | |



ELECTRICAL CHARACTERISTICS (continued)

(Circuit of Figure 1, V_{DD} = +3.3V, V_{BATT} = +16.8V, V_{DCIN} = +18V, **T_A** = 0°C to +85°C, unless otherwise noted. Typical values are at T_A = +25°C.)

| PARAMETER | SYMBOL | CONDITIONS | MIN | ТҮР | MAX | UNITS |
|---|-------------|--|------|-------|------|----------------------|
| DC-TO-DC CONVERTER SPECIF | ICATIONS | 1 | | | | |
| Minimum Off-Time | toff | | 1.0 | 1.25 | 1.5 | μs |
| Maximum On-Time | ton | | 5 | 10 | 15 | ms |
| Maximum Duty Cycle | | | 99 | 99.99 | | % |
| LX Input Bias Current | | $V_{DCIN} = 28V, V_{BATT} = V_{LX} = 20V$ | | 200 | 500 | μA |
| LX Input Quiescent Current | | $V_{DCIN} = 0$, $V_{BATT} = V_{LX} = 20V$ | | | 1 | μA |
| BST Supply Current | | DHI high | | 6 | 15 | μΑ |
| DLOV Supply Current | | V _{DLOV} = V _{LDO} , DLO low | | 5 | 10 | μA |
| DHI Output Resistance | | DHI high or low, V_{BST} - V_{LX} = 4.5V | | 6 | 14 | Ω |
| DLO Output Resistance | | DLO high or low, $V_{DLOV} = 4.5V$ | | 6 | 14 | Ω |
| THERMISTOR COMPARATOR SI | PECIFICATIO | INS | | | | |
| THM Input Bias Current | | V_{THM} = 4% of V_{DD} to 96% of V_{DD} , V_{DD} = 2.8V to 5.65V | -1 | | +1 | μA |
| Thermistor Overrange Threshold | | $V_{DD} = 2.8V$ to 5.65V, V_{THM} falling | 89.5 | 91 | 92.5 | % of V _{DI} |
| Thermistor Cold Threshold | | $V_{DD} = 2.8V$ to 5.65V, V_{THM} falling | 74 | 75.5 | 77 | % of V _{DI} |
| Thermistor Hot Threshold | | V_{DD} = 2.8V to 5.65V, V_{THM} falling | 22 | 23.5 | 25 | % of V _{DI} |
| Thermistor Underrange Threshold | | $V_{DD} = 2.8V$ to 5.65V, V_{THM} falling | 6 | 7.5 | 9 | % of V _{DI} |
| Thermistor Comparator Threshold Hysteresis | | All four comparators, $V_{DD} = 2.8V$ to 5.65V | | 1 | | % of V _{DI} |
| SMB INTERFACE LEVEL SPECIF | | / _{DD} = 2.8V to 5.65V) | | | | |
| SDA/SCL Input Low Voltage | | | | | 0.6 | V |
| SDA/SCL Input High Voltage | | | 1.4 | | | V |
| SDA/SCL Input Hysteresis | | | | 220 | | mV |
| SDA/SCL Input Bias Current | | | -1 | | +1 | μA |
| SDA Output Low Sink Current | | $V_{SDA} = 0.4V$ | 6 | | | mA |
| INT Output High Leakage | | $V_{\overline{INT}} = 5.65V$ | | | 1 | μA |
| INT Output Low Voltage | | $I_{\overline{INT}} = 1mA$ | | 25 | 200 | mV |
| SMB INTERFACE TIMING SPECI | FICATIONS (| V_{DD} = 2.8V to 5.65V, Figures 4 and 5) | | | | |
| SCL High Period | thigh | | 4 | | | μs |
| SCL Low Period | tLOW | | 4.7 | | | μs |
| Start Condition Setup Time from SCL | tsu:sta | | 4.7 | | _ | μs |
| Start Condition Hold Time from SCL | thd:sta | | 4 | | | μs |
| SDA Setup Time from SCL | tsu:dat | | 250 | | | ns |
| SDA Hold Time from SCL | thd:dat | | 0 | | | ns |

M/X/W

ELECTRICAL CHARACTERISTICS (continued)

(Circuit of Figure 1, V_{DD} = +3.3V, V_{BATT} = +16.8V, V_{DCIN} = +18V, **T_A** = 0°C to +85°C, unless otherwise noted. Typical values are at T_A = +25°C.)

| PARAMETER | SYMBOL | CONDITIONS | MIN | ТҮР | MAX | UNITS |
|--|-----------------|------------|-----|-----|-----|-------|
| SDA Output Data Valid from SCL | t _{DV} | | | | 1 | μs |
| Maximum Charge Period Without a ChargingVoltage() or Charging Current() Loaded | twdt | | 140 | 175 | 210 | S |

ELECTRICAL CHARACTERISTICS

(Circuit of Figure 1, V_{DD} = +3.3V, V_{BATT} = +16.8V, V_{DCIN} = +18V, T_A = -40°C to +85°C, unless otherwise noted. Guaranteed by design.)

| PARAMETER | SYMBOL | CONDIT | MIN | ТҮР | МАХ | UNITS | |
|--|-----------------|--|-----------------------------|------|-------|-------|----|
| GENERAL SPECIFICATIONS | | • | | • | | | |
| DCIN Typical Operating Range | VDCIN | | | 8 | | 28 | V |
| DCIN Supply Current | IDCIN | $8V < V_{DCIN} < 28V$ | | | | 6 | mA |
| DCIN Supply Current Charging Inhibited | | 8V < V _{DCIN} < 28V | 20 | | | | mA |
| DCIN Undervoltage Threshold | | When AC_PRESENT switches | DCIN rising DCIN falling | 7 | | 7.85 | V |
| LDO Output Voltage V _{LDO} 8V < V | | 8V < V _{DCIN} < 28V, 0 < I | LDO < 15mA | 5.15 | | 5.65 | V |
| V _{DD} Input Voltage Range | | 8V < V _{DCIN} < 28V (Note | | 2.80 | | 5.65 | V |
| V _{DD} Undervoltage Threshold | | When the SMB responds to commands | V _{DD} rising | 2.1 | | 2.8 | V |
| V _{DD} Quiescent Current | I _{DD} | $0 < V_{DCIN} < 6V, V_{DD} = 0$ $V_{SDA} = 5V$ | 2.1 | | 150 | μA | |
| REF Output Voltage | VREF | 0 < I _{REF} < 200µA | 4.035 | | 4.157 | V | |
| BATT Undervoltage Threshold | | When ICHARGE drops to | 128mA (Note 2) | 2.4 | | 2.8 | V |
| PDS Charging Source Switch Turn-Off Threshold | VPDS-OFF | V_{CVS} referred to V_{BATT} , | V _{CVS} falling | 50 | | 150 | mV |
| PDS Charging Source Switch Threshold Hysteresis | VPDS-HYS | V_{CVS} referred to V_{BATT} | | 100 | | 300 | mV |
| PDS Output Low Voltage, PDS Below CSSP | | IPDS = 0 | | 8 | | 12 | V |
| PDS Turn-On Current | | PDS = CSSP | | 100 | | 300 | μA |
| PDS Turn-Off Current | | VPDS = VCSSP - 2V, VDC | CIN = 16V | 10 | | | mA |
| PDL Load Switch Turn-Off Threshold | VPDL-OFF | V_{CVS} referred to V_{BATT} , | -150 | | -50 | mV | |
| PDL Load Switch Threshold Hysteresis | VPDL-HYS | V_{CVS} referred to V_{BATT} | | 100 | | 300 | mV |
| PDL Turn-Off Current | | V _{CSSN} - V _{PDL} = 1V | | 6 | | | mA |

ELECTRICAL CHARACTERISTICS (continued)

(Circuit of Figure 1, V_{DD} = +3.3V, V_{BATT} = +16.8V, V_{DCIN} = +18V, T_A = -40°C to +85°C, unless otherwise noted. Guaranteed by design.)

| PARAMETER | SYMBOL | CO | NDITIONS | MIN | TYP | MAX | UNITS | | | | |
|---|--------|--|---|-------------|------|--------|-------|--|--|--|--|
| PDL Turn-On Resistance | | PDL to GND | | 50 | | 150 | kΩ | | | | |
| CVS Input Bias Current | | $V_{CVS} = 28V$ | | | | 20 | μA | | | | |
| ERROR AMPLIFIER SPECIFICA | TIONS | | | • | | | | | | | |
| | | ChargingVoltage() | = 0x41A0 | 16.532 | | 17.068 | | | | | |
| | 1/0 | ChargingVoltage() | = 0x3130 | 12.391 | | 12.793 | V | | | | |
| BATT Full-Charge Voltage | VO | ChargingVoltage() | = 0x20D0 | 8.266 8.534 | | | V | | | | |
| | | ChargingVoltage() | = 0x1060 | 4.124 | | 4.260 | | | | | |
| BATT Charge Current-Sense | | | ChargingCurrent() = 0x0BC0 | 130.4 | | 170.4 | | | | | |
| Voltage | 10 | VCSIP - VCSIN | ChargingCurrent() = 0x0080 | 0.76 | | 12.04 | mV | | | | |
| DCIN Source Current-Limit | | | V _{CLS} = 4.096V | 174.3 | | 235.3 | | | | | |
| Sense Voltage | | VCSSP - VCSSN | V _{CLS} = 2.048V | 82.2 | | 120.2 | mV | | | | |
| BATT Undervoltage Charge Current-Sense Voltage | | V _{BATT} = 1V, V _{CSIP} | - V _{CSIN} | 1 | | 10 | mV | | | | |
| Inductor Peak Current Limit | | VCSIP - VCSIN | | 250 | | 350 | mV | | | | |
| BATT/CSIP/CSIN Input Voltage Range | | | 0 | | 20 | V | | | | | |
| Total BATT Input Bias Current | | Total of I _{BATT} , I _{CSIF} V _{BATT} = 0 to 20V | -700 | | +700 | μA | | | | | |
| Total BATT Quiescent Current | | Total of IBATT, ICSIF VBATT = 0 to 20V, c | , and I _{CSIN} ; charge inhibited | -100 | | +100 | μA | | | | |
| Total BATT Standby Current | | Total of IBATT, ICSIF VBATT = 0 to 20V, V | | -5 | | +5 | μA | | | | |
| CSSP/Input Bias Current | | VCSSP = VCSSN = V | / _{DCIN} = 0 to 28V | -100 | | +1000 | μA | | | | |
| CSSN Input Bias Current | | VCSSP = CCSSN = V | VDCIN = 0 to 28V | -100 | | +100 | mA | | | | |
| CSSP/CSSN Quiescent Current | | $V_{CSSP} = V_{CSSN} = 2$ | 28V, V _{DCIN} = 0 | -1 | | +1 | μA | | | | |
| Battery Voltage-Error Amp DC Gain | | From BATT to CCV | | 200 | | | V/V | | | | |
| CLS Input Bias Current | | $V_{CLS} = V_{REF}/2$ to V | REF | -1 | | +1 | μA | | | | |
| Battery Voltage-Error Amp Transconductance | | From BATT to CCV $0x41A0$, $V_{BATT} = 1$ | , ChargingVoltage() = 6.8V | 0.111 | | 0.444 | µA/mV | | | | |
| Battery Current-Error Amp Transconductance | | From CSIP/CSIN to = $0x0BC0$, V_{CSIP} - | CCI, ChargingCurrent() V _{CSIN} = 150.4mV | 0.5 | | 2.0 | µA/mV | | | | |
| Input Current-Error Amp Transconductance | | From CSSP/CSSN t VCSSP - VCSSN = 1 | to CCS, V _{CLS} = 2.048V, 02.4mV | 0.5 | | 2.0 | µA/mV | | | | |
| CCV/CCI/CCS Clamp Voltage | | | cs = 0.25V to 2V (Note 3) | 150 | | 600 | mV | | | | |

M/IXI/M

ELECTRICAL CHARACTERISTICS (continued)

(Circuit of Figure 1, V_{DD} = +3.3V, V_{BATT} = +16.8V, V_{DCIN} = +18V, T_A = -40°C to +85°C, unless otherwise noted. Guaranteed by design.)

| PARAMETER | SYMBOL | CONDITIONS | MIN | ТҮР | МАХ | UNITS |
|--|-------------|---|------|-----|------|----------------------|
| DC-TO-DC CONVERTER SPECIF | ICATIONS | · | | | | |
| Minimum Off-Time | tOFF | | 1.0 | | 1.5 | μs |
| Maximum On-Time | ton | | 5 | | 15 | ms |
| Maximum Duty Cycle | | | 99 | | | % |
| LX Input Bias Current | | $V_{\text{DCIN}} = 28V, V_{\text{BATT}} = V_{\text{LX}} = 20V$ | | | 500 | μΑ |
| LX Input Quiescent Current | | $V_{DCIN} = 0$, $V_{BATT} = V_{LX} = 20V$ | | | 1 | μΑ |
| BST Supply Current | | DHI high | | | 15 | μΑ |
| DLOV Supply Current | | $V_{DLOV} = V_{LDO}$, DLO low | | | 10 | μΑ |
| DHI Output Resistance | | DHI high or low, $V_{BST} - V_{LX} = 4.5V$ | | | 14 | Ω |
| DLO Output Resistance | | DLO high or low, $V_{DLOV} = 4.5V$ | | | 14 | Ω |
| THERMISTOR COMPARATOR SI | PECIFICATIO | DNS | | | | |
| THM Input Bias Current | | V_{THM} = 4% of V_{DD} to 96% of V_{DD} , V_{DD} = 2.8V to 5.65V | -1 | | +1 | μΑ |
| Thermistor Overrange Threshold | | $V_{DD} = 2.8V$ to 5.65V, V_{THM} falling | 89.5 | | 92.5 | % of V _{DD} |
| Thermistor Cold Threshold | | $V_{DD} = 2.8V$ to 5.65V, V_{THM} falling | 74 | | 77 | % of V _{DD} |
| Thermistor Hot Threshold | | V_{DD} = 2.8V to 5.65V, V_{THM} falling | 22 | | 25 | % of V _{DD} |
| Thermistor Underrange Threshold | | V_{DD} = 2.8V to 5.65V, V_{THM} falling | 6 | | 9 | % of V _{DD} |
| SMB INTERFACE LEVEL SPECIF | | V _{DD} = 2.8V to 5.65V) | | | | |
| SDA/SCL Input Low Voltage | | | | | 0.6 | V |
| SDA/SCL Input High Voltage | | | 1.4 | | | V |
| SDA/SCL Input Bias Current | | | -1 | | +1 | μA |
| SDA Output Low Sink Current | | $V_{SDA} = 0.4V$ | 6 | | | mA |
| INT Output High Leakage | | $V_{\overline{INT}} = 5.65V$ | | | 1 | μΑ |
| INT Output Low Voltage | | ITNT = 1mA | | | 200 | mV |
| SMB INTERFACE TIMING SPECI | FICATIONS (| V_{DD} = 2.8V to 5.65V, Figures 4 and 5) | | | | |
| SCL High Period | thigh | | 4 | | | μs |
| SCL Low Period | tLOW | | 4.7 | | | μs |
| Start Condition Setup Time from SCL | tsu:sta | | 4.7 | | | μs |
| Start Condition Hold Time from SCL | thd:sta | | 4 | | | μs |
| SDA Setup Time from SCL | tsu:dat | | 250 | | | ns |
| SDA Hold Time from SCL | thd:dat | | 0 | | | ns |

ELECTRICAL CHARACTERISTICS (continued)

(Circuit of Figure 1, $V_{DCIN} = 20V$, $T_A = +25^{\circ}C$, unless otherwise noted.)

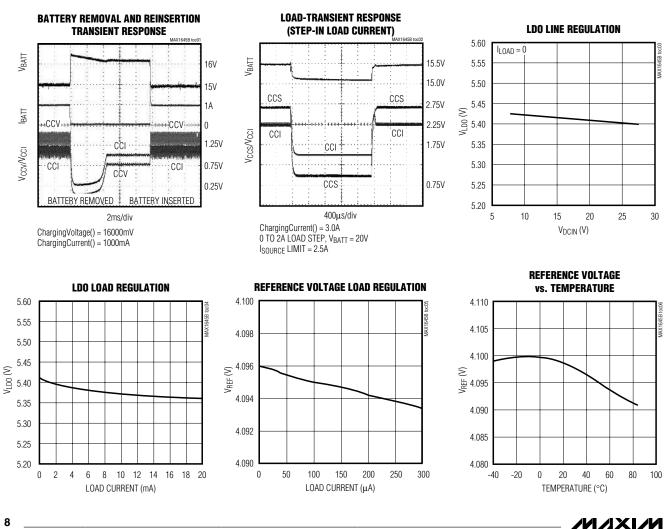
(Circuit of Figure 1, V_{DD} = +3.3V, V_{BATT} = +16.8V, V_{DCIN} = +18V, T_A = -40°C to +85°C, unless otherwise noted. Guaranteed by design.)

| PARAMETER | SYMBOL | CONDITIONS | MIN | ТҮР | MAX | UNITS |
|--|-----------------|------------|-----|-----|-----|-------|
| SDA Output Data Valid from SCL | t _{DV} | | | | 1 | μs |
| Maximum Charge Period Without a ChargingVoltage() or Charging Current() Loaded | twdt | | 140 | | 210 | s |

Note 1: Guaranteed by meeting the SMB timing specs.

Note 2: The charger reverts to a trickle-charge mode of ICHARGE = 128mA below this threshold.

Note 3: Voltage difference between CCV and CCI or CCS when one of these three pins is held low and the others try to pull high.

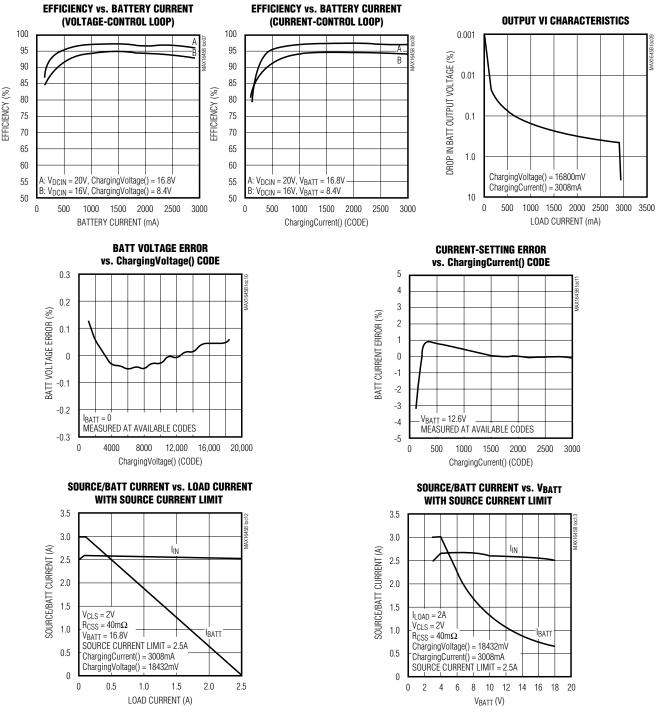


Typical Operating Characteristics

MAX1645B

Typical Operating Characteristics (continued)

(Circuit of Figure 1, V_{DCIN} = 20V, T_A = +25°C, unless otherwise noted.)



M/IXI/M

MAX1645B

Pin Description

| | 1 | - - |
|-----|-----------------|---|
| PIN | NAME | FUNCTION |
| 1 | DCIN | DC Supply Voltage Input |
| 2 | LDO | 5.4V Linear-Regulator Voltage Output. Bypass with a 1µF capacitor to GND. |
| 3 | CLS | Source Current-Limit Input |
| 4 | REF | 4.096V Reference Voltage Output |
| 5 | CCS | Charging Source Compensation Capacitor Connection. Connect a 0.01µF capacitor from CCS to GND. |
| 6 | CCI | Battery Current-Loop Compensation Capacitor Connection. Connect a 0.01µF capacitor from CCI to GND. |
| 7 | CCV | Battery Voltage-Loop Compensation Capacitor Connection. Connect a $10k\Omega$ resistor in series with a 0.01μ F capacitor to GND. |
| 8 | GND | Ground |
| 9 | BATT | Battery Voltage Output |
| 10 | DAC | DAC Voltage Output |
| 11 | V _{DD} | Logic Circuitry Supply Voltage Input (2.8V to 5.65V) |
| 12 | THM | Thermistor Voltage Input |
| 13 | SCL | SMB Clock Input |
| 14 | SDA | SMB Data Input/Output. Open-drain output. Needs external pullup. |
| 15 | ĪNT | Interrupt Output. Open-drain output. Needs external pullup. |
| 16 | PDL | PMOS Load Switch Driver Output |
| 17 | CSIN | Battery Current-Sense Negative Input |
| 18 | CSIP | Battery Current-Sense Positive Input |
| 19 | PGND | Power Ground |
| 20 | DLO | Low-Side NMOS Driver Output |
| 21 | DLOV | Low-Side NMOS Driver Supply Voltage. Bypass with 0.1µF capacitor to GND. |
| 22 | LX | Inductor Voltage Sense Input |
| 23 | DHI | High-Side NMOS Driver Output |
| 24 | BST | High-Side Driver Bootstrap Voltage Input. Bypass with 0.1µF capacitor to LX. |
| 25 | CSSN | Charging Source Current-Sense Negative Input |
| 26 | CSSP | Charging Source Current-Sense Positive Input |
| 27 | PDS | Charging Source PMOS Switch Driver Output |
| 28 | CVS | Charging Source Voltage Input |

Detailed Description

The MAX1645B consists of current-sense amplifiers, an SMBus interface, transconductance amplifiers, reference circuitry, and a DC-DC converter (Figure 2). The DC-DC converter generates the control signals for the external MOSFETs to maintain the voltage and the current set by the SMBus interface. The MAX1645B features a voltageregulation loop and two current-regulation loops. The loops operate independently of each other. The voltageregulation loop monitors BATT to ensure that its voltage never exceeds the voltage set point (V0). The battery current-regulation loop monitors current delivered to BATT to ensure that it never exceeds the current-limit set point (I0). The battery current-regulation loop is in control as long as BATT voltage is below V0. When BATT voltage reaches V0, the current loop no longer regulates. A third loop reduces the battery-charging current when the sum of the system (the main load) and the battery charger input current exceeds the charging source current limit.

Setting Output Voltage

The MAX1645B voltage DAC has a 16mV LSB and an 18.432V full scale. The SMBus specification allows for a 16-bit ChargingVoltage() command that translates to a 1mV LSB and a 65.535V full-scale voltage; therefore, the ChargingVoltage() value corresponds to the output voltage in millivolts. The MAX1645B ignores the first 4 LSBs and uses the next 11 LSBs to control the voltage DAC. All codes greater than or equal to 0x4800 (18432mV) result in a voltage overrange, limiting the charger voltage to 18.432V. All codes below 0x0400 (1024mV) terminate charging.

Setting the Charge Current

The MAX1645B charge-current DAC has a 3.2mV to 150.4mV range. The SMBus specification allows for a 16-bit ChargingCurrent() command that translates to a 0.05mV LSB and a 3.376V full-scale current-sense voltage. The MAX1645B drops the first 6 LSBs and uses the remaining 6 MSBs to control the charge-current DAC. All codes above 0x0BC0 result in an overrange condition, limiting the charge current-sense voltage to 150.4mV. All codes below 0x0080 turn off the charging current. Therefore, the charging current (ICHARGE) is determined by:

$I_{CHARGE} = V_{DACI} / R_{CSI}$

where V_{DACI} is the current-sense voltage set by ChargingCurrent(), and R_{CSI} is the battery currentsense resistor (R2 in Figure 1). When using a 50m Ω current-sense resistor, the ChargingCurrent() value corresponds directly to the charging current in milliamps (0x0400 = 1024mA = 52.2mV/50m Ω).

Input Current Limiting

The MAX1645B limits the current drawn by the charger when the load current becomes high. The device limits the charging current so the AC adapter voltage is not loaded down. An internal amplifier, CSS, compares the voltage between CSSP and CSSN to the voltage at CLS/20. VCLS is set by a resistor-divider between REF and GND.

The input source current is the sum of the device current, the charge input current, and the load current. The device current is minimal (6mA max) in comparison to the charge and load currents. The charger input current is generated by the DC-DC converter; therefore, the actual source current required is determined as follows:

ISOURCE = ILOAD + [(ICHARGE × VBATT) / (VIN ×
$$\eta$$
)]

where η is the efficiency of the DC-DC converter (typically 85% to 95%).

V_{CLS} determines the threshold voltage of the CSS comparator. R3 and R4 (Figure 1) set the voltage at CLS. Sense resistor R1 sets the maximum allowable source current. Calculate the maximum current as follows:

$$I_{MAX} = V_{CLS} / (20 \times R_1)$$

(Limit $V_{\mbox{CSSP}}$ - $V_{\mbox{CSSN}}$ to between 102.4mV and 204.8mV.)

The configuration in Figure 1 provides an input current limit of:

$$I_{MAX} = (2.048 V / 20) / 0.04 \Omega = 2.56 A$$

LDO Regulator

An integrated LDO regulator provides a +5.4V supply derived from DCIN, which can deliver up to 15mA of current. The LDO sets the gate-drive level of the NMOS switches in the DC-DC converter. The drivers are actually powered by DLOV and BST, which must be connected to LDO through a lowpass filter and a diode as shown in Figure 1. Also see the *MOSFET Drivers* section. The LDO also supplies the 4.096V reference and most of the control circuitry. Bypass LDO with a 1µF capacitor.

VDD Supply

This input provides power to the SMBus interface and the thermistor comparators. Typically connect V_{DD} to LDO or, to keep the SMBus interface of the MAX1645B active while the supply to DCIN is removed, connect an external supply to V_{DD}.



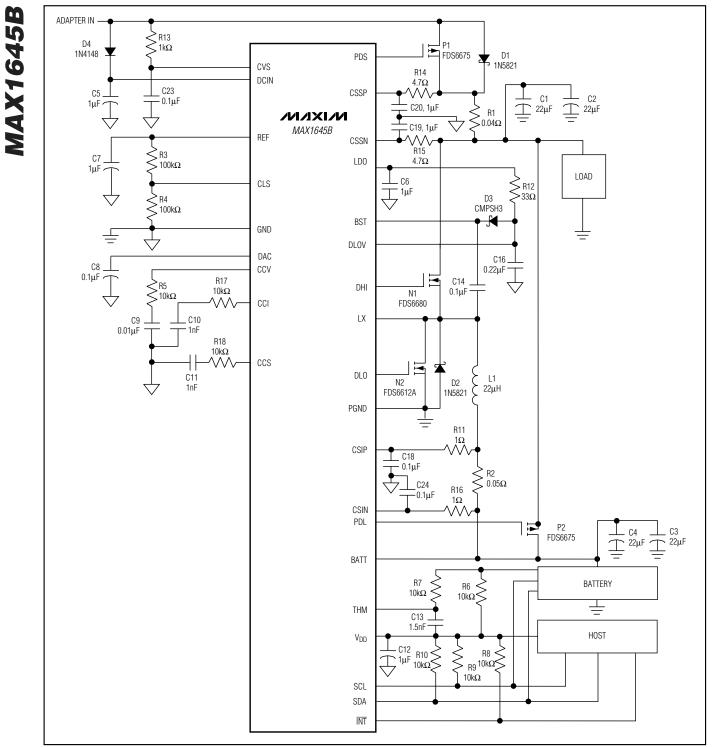
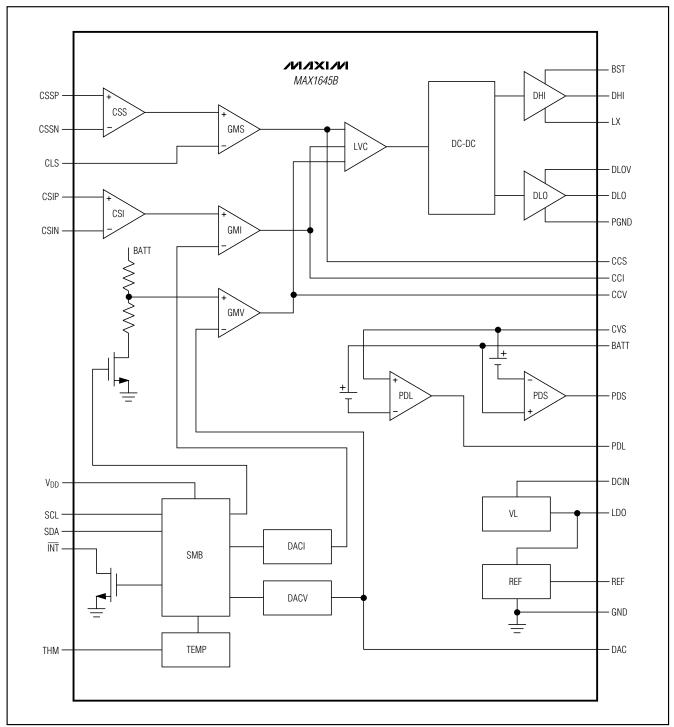


Figure 1. Typical Application Circuit



M/X/W

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MAX1645B

MAX1645B

Operating Conditions

The MAX1645B changes its operation depending on the voltages at DCIN, BATT, V_{DD} , and THM. Several important operating states follow:

- AC Present. When DCIN is >7.5V, the battery is considered to be in an AC present state. In this condition, both the LDO and REF function properly and battery charging is allowed. When AC is present, the AC_PRESENT bit (bit 15) in the ChargerStatus() register is set to 1.
- **Power Fail.** When DCIN is <BATT + 0.3V, the part is in the power-fail state, since the charger does not have enough input voltage to charge the battery. In power fail, the PDS input PMOS switch is turned off and the POWER_FAIL bit (bit 13) in the ChargerStatus() register is set to 1.
- Battery Present. When THM is <91% of V_{DD}, the battery is considered to be present. The MAX1645B uses the THM pin to detect when a battery is connected to the charger. When the battery is present, the BATTERY_PRESENT bit (bit 14) in the ChargerStatus() register is set to 1 and charging can proceed. When the battery is not present, all of the registers are reset. With no battery present, the charger performs a "float" charge to minimize contact arcing on battery connection. The "float" charge still tries to regulate the BATT pin voltage at 18.32V with 128mA of current compliance.
- **Battery Undervoltage.** When BATT <2.5V, the battery is in an undervoltage state. This causes the charger to reduce its current compliance to 128mA. The content of the ChargingCurrent() register is unaffected and, when the BATT voltage exceeds 2.7V, normal charging resumes. ChargingVoltage() is unaffected and can be set as low as 1.024V.
- **Vpp Undervoltage.** When V_{DD} <2.5V, the V_{DD} supply is in an undervoltage state, and the SMBus interface does not respond to commands. Coming out of the undervoltage condition, the part is in its Power-On Reset state. No charging occurs when V_{DD} is under voltage.

SMBus Interface

The MAX1645B receives control inputs from the SMBus interface. The serial interface complies with the SMBus specification (refer to the System Management Bus Specification from Intel Corporation). Charger functionality complies with the Intel/Duracell Smart Charger Specification for a Level 2 charger.

The MAX1645B uses the SMBus read-word and writeword protocols to communicate with the battery being charged, as well as with any host system that monitors the battery-to-charger communications as a Level 2 SMBus charger. The MAX1645B is an SMBus slave device and does not initiate communication on the bus. It receives commands and responds to queries for status information. Figure 3 shows examples of the SMBus write-word and read-word protocols, and Figures 4 and 5 show the SMBus serial-interface timing.

Each communication with this part begins with the MASTER issuing a START condition that is defined as a falling edge on SDA with SCL high and ends with a STOP condition defined as a rising edge on SDA with SCL high. Between the START and STOP conditions, the device address, the command byte, and the data bytes are sent. The MAX1645B's device address is 0x12 and supports the charger commands as described in Tables 1–6.

Battery Charger Commands

ChargerSpecInfo()

The ChargerSpecInfo() command uses the read-word protocol (Figure 3b). The command code for ChargerSpecInfo() is 0x11 (0b00010001). Table 1 lists the functions of the data bits (D0–D15). Bit 0 refers to the D0 bit in the read-word protocol. The MAX1645B complies with Level 2 Smart Battery Charger Specification Revision 1.0; therefore, the ChargerSpecInfo() command returns 0x09.

ChargerMode()

The ChargerMode() command uses the write-word protocol (Figure 3a). The command code for ChargerMode() is 0x12 (0b00010010). Table 2 lists the functions of the data bits (D0–D15). Bit 0 refers to the D0 bit in the write-word protocol.

To charge a battery that has a thermistor impedance in the HOT range (i.e., THERMISTOR_HOT = 1 and THERMISTOR_UR = 0), the host must use the ChargerMode() command to clear HOT_STOP after the battery is inserted. The HOT_STOP bit returns to its default power-up condition (1) whenever the battery is removed.

ChargerStatus()

The ChargerStatus() command uses the read-word protocol (Figure 3b). The command code for ChargerStatus() is 0x13 (0b00010011). Table 3 describes the functions of the data bits (D0–D15). Bit 0 refers to the D0 bit in the read-word protocol.

The ChargerStatus() command returns information about thermistor impedance and the MAX1645B's internal state. The latched bits, THERMISTOR_HOT and ALARM_INHIBITED, are cleared whenever BATTERY_ PRESENT = 0 or ChargerMode() is written with POR_RESET = 1. The ALARM_INHIBITED status bit can also be cleared by writing a new charging current OR charging voltage.

| S | SLAVE ADDRESS | w | AC | K COMMAN BYTE | D | | АСК | LC DA BY | ТΑ | AC | K D | IIGH ATA YTE | AC | к р | | | |
|------------|---|------------------------|------------------|---|-------------------|-----|-----|-------------------------------|------|-----|----------------|--------------------|-----|-------------------|-----|------|---|
| | 7 bits | 1b | 1b | 8 bits | | | 1b | 8 b | oits | 1b | 8 | bits | 1 | b | | | |
| | MSB LSB | 0 | 0 | MSB LSI | В | | 0 | MSB | LSE | 3 0 | MSI | B LSE | 3 (|) | | | |
| L \ | Preset to 0b0001001 | Fai | | ChargerMode() = ChargingCurrent(ChargerVoltage() AlarmWarning() = |) = 0x1 = 0x15 | | | D7 | D | 0 | D15 | C | 8 | | | | |
| D) S | Read-Word SLAVE ADDRESS | | ACK | COMMAND BYTE | АСК | S | | AVE RESS | R | АСК | LO DA BY | ГА | АСК | HIG DAT BYT | Α | NACK | |
| | 7 bits | 1b | 1b | 8 bits | 1b | | 7 | oits | 1b | 1b | 8 b | its | 1b | 8 bi | ts | 1b | t |
| | MSB LSB | 0 | 0 | MSB LSB | 0 | | MSB | LSB | 1 | 0 | MSB | LSB | 0 | MSB | LSB | 1 | |
| | Preset to 0b0001001 | | | ChargerSpecInfo() = 0x11 ChargerStatus() = 0x13 | | | | eset to 00100 ⁻ | 1 | | D7 | D | 0 | D15 | D | 8 | |
| S A | CK = Acknow / = Write Bit (MASTE | vledo logic R TC | ge (logi low) | E | NA | ACK | | | | 0 (| ogic hig | h) | | | | | |

Figure 3. SMBus Write-Word and Read-Word Protocols

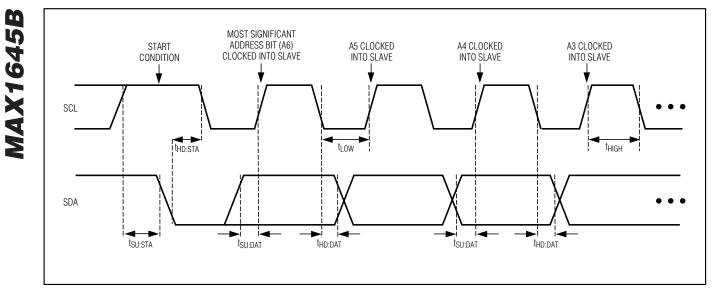


Figure 4. SMBus Serial Interface Timing—Address

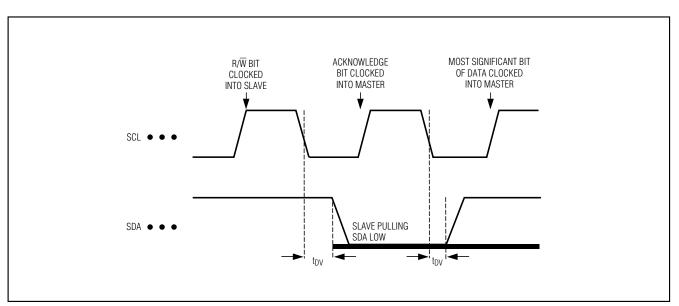


Figure 5. SMBus Serial Interface Timing—Acknowledgment

Table 1. ChargerSpecInfo()*

| BIT | NAME | DESCRIPTION |
|-----|------------------|--|
| 0 | CHARGER_SPEC | Returns a 1 for version 1.0 |
| 1 | CHARGER_SPEC | Returns a zero for version 1.0 |
| 2 | CHARGER_SPEC | Returns a zero for version 1.0 |
| 3 | CHARGER_SPEC | Returns a 1 for version 1.0 |
| 4 | SELECTOR_SUPPORT | Returns a zero, indicating no smart battery selector functionality |
| 5 | Reserved | Returns a zero |
| 6 | Reserved | Returns a zero |
| 7 | Reserved | Returns a zero |
| 8 | Reserved | Returns a zero |
| 9 | Reserved | Returns a zero |
| 10 | Reserved | Returns a zero |
| 11 | Reserved | Returns a zero |
| 12 | Reserved | Returns a zero |
| 13 | Reserved | Returns a zero |
| 14 | Reserved | Returns a zero |
| 15 | Reserved | Returns a zero |

*Command: 0x11

Table 2. ChargerMode()*

MAX1645B

| BIT | NAME | FUNCTION | |
|-----|-----------------------|--|--|
| 0 | INHIBIT_CHARGE | 0* = Allow normal operation; clear the CHG_INHIBITED flip-flop. 1 = Turn off the charger; set the CHG_INHIBITED flip-flop. The CHG_INHIBITED flip-flop is not affected by any other commands. | |
| 1 | ENABLE_POLLING | Not implemented. | |
| 2 | POR_RESET | 0 = No change. 1 = Change the ChargingVoltage() to 0xFFFF and the ChargingCurrent() to 0x00C0; clear the THERMISTOR_HOT and ALARM_INHIBITED flip-flops. | |
| 3 | RESET_TO_ZERO | Not implemented. | |
| 4 | AC_PRESENT_MASK | 0* = Interrupt on either edge of the AC_PRESENT status bit. 1 = Do not interrupt because of an AC_PRESENT bit change. | |
| 5 | BATTERY_PRESENT_ MASK | 0* = Interrupt on either edge of the BATTERY_PRESENT status bit. 1 = Do not interrupt because of a BATTERY_PRESENT bit change. | |
| 6 | POWER_FAIL_MASK | 0* = Interrupt on either edge of the POWER_FAIL status bit. 1 = Do not interrupt because of a POWER_FAIL bit change. | |
| 7 | — | Not implemented. | |
| 8 | _ | Not implemented. | |
| 9 | | Not implemented. | |
| 10 | HOT_STOP | 0 = The THERMISTOR_HOT status bit does not turn off the charger. 1* = The THERMISTOR_HOT status bit does turn off the charger. THERMISTOR_HOT is reset by either POR_RESET or BATTERY_PRESENT = 0 status bit. | |
| 11 | _ | Not implemented. | |
| 12 | _ | Not implemented. | |
| 13 | — | Not implemented. | |
| 14 | | Not implemented. | |
| 15 | — | Not implemented. | |

*Command: 0x12

*State at chip initial power-on (i.e., V_{DD} from 0 to +3.3V).

Table 3. ChargerStatus()*

| BIT | NAME | FUNCTION | |
|-----|------------------|---|--|
| 0 | CHARGE_INHIBITED | 0** = Ready to charge smart battery. 1 = Charger is inhibited, I(chg) = 0mA. This status bit returns the value of the CHG_INHIBITED flip-flop. | |
| 1 | MASTER_MODE | Always returns zero. | |
| 2 | VOLTAGE_NOT_REG | Function disabled. Always returns zero. | |
| 3 | CURRENT_NOT_REG | Function disabled. Always returns zero. | |
| 4 | LEVEL_2 | Always returns a 1. | |
| 5 | LEVEL_3 | Always returns a zero. | |
| 6 | CURRENT_OR | 0** = The ChargingCurrent() value is valid for the MAX1645B. 1 = The ChargingCurrent() value exceeds the MAX1645B output range, i.e., programmed ChargingCurrent() exceeds 3008mA. | |
| 7 | VOLTAGE_OR | 0 = The ChargingVoltage() value is valid for the MAX1645B. 1** = The ChargingVoltage() value exceeds the MAX1645B output range, i.e., programmed ChargingVoltage() exceeds 1843mV. | |
| 8 | THERMISTOR_OR | 0 = THM is <91% of the reference voltage. 1 = THM is >91% of the reference voltage. | |
| 9 | THERMISTOR_COLD | 0 = THM is <75.5% of the reference voltage. 1 = THM is >75.5% of the reference voltage. | |
| 10 | THERMISTOR_HOT | 0 = THM has not dropped to <23.5% of the reference voltage. 1 = THM has dropped to <23.5% of the reference voltage. THERMISTOR_HOT flip-flop cleared by BATTERY_PRESENT = 0 or writing a 1 into the POR_RESET bit in the ChargerMode() command. | |
| 11 | THERMISTOR_UR | 0 = THM is >7.5% of the reference voltage. 1 = THM is <7.5% of the reference voltage. | |
| 12 | ALARM_INHIBITED | Returns the state of the ALARM_INHIBITED flip-flop. This flip-flop is set by either a watchdog timeout or by writing an AlarmWarning() command with bits 11, 12, 13, 14, or 15 set. This flip-flop is cleared by BATTERY_PRESENT = 0, writing a 1 into the POR_RESET bit in the ChargerMode() command, or by receiving successive ChargingVoltage() and ChargingCurrent() commands. POR: 0. | |
| 13 | POWER_FAIL | 0 = The charging source voltage CVS is above the BATT voltage. 1 = The charging source voltage CVS is below the BATT voltage. | |
| 14 | BATTERY_PRESENT | 0 = No battery is present (based on THM input). 1 = Battery is present (based on THM input). | |
| 15 | AC_PRESENT | 0 = DCIN is below the 7.5V undervoltage threshold. 1 = DCIN is above the 7.5V undervoltage threshold. | |

MAX1645B

*Command: 0x13

**State at chip initial power-on.

Table 4. ChargingCurrent()*

| BIT | NAME | FUNCTION | |
|-------|------------------------|--|--|
| 0 | — | Not used. Normally a 0.05mV (1mA x 50m Ω) weight. | |
| 1 | — | Not used. Normally a 0.1mV (2mA x 50m Ω) weight. | |
| 2 | _ | Not used. Normally a 0.2mV (4mA x 50m Ω) weight. | |
| 3 | _ | Not used. Normally a 0.4mV (8mA x 50m Ω) weight. | |
| 4 | — | Not used. Normally a 0.8mV (16mA x 50m Ω) weight. | |
| 5 | — | Not used. Normally a 1.6mV (32mA x 50m Ω) weight. | |
| 6 | Charge Current, DACI 0 | 0 = Adds 0mV of charge current-sense voltage. $1 = Adds 3.2mV (64mA x 50m\Omega) charge current-sense voltage.$ 6.4mV (min) (128mA x 50mA) sense voltage. | |
| 7 | Charge Current, DACI 1 | 0 = Adds 0mV of charge current-sense voltage. 1 = Adds 6.4mV (128mA x 50m Ω) charge current-sense voltage. | |
| 8 | Charge Current, DACI 2 | 0 = Adds 0mV of charge current-sense voltage. 1 = Adds 12.8mV (256mA x 50m Ω) charge current-sense voltage. | |
| 9 | Charge Current, DACI 3 | 0 = Adds 0mV of charge current-sense voltage. 1 = Adds 25.6mV (512mA x 50m Ω) charge current-sense voltage. | |
| 10 | Charge Current, DACI 4 | 0 = Adds 0mV of charge current-sense voltage. 1 = Adds 51.2mV (1024mA x 50mΩ) charge current-sense voltage. | |
| 11 | Charge Current, DACI 5 | 0 = Adds 0mV of charge current-sense voltage. 1 = Adds 102.4mV (2048mA x 50m Ω) charge current-sense voltage. 150.4mV (max) (3008mA x 50mA) sense voltage. | |
| 12–15 | _ | 0 = Adds 0mV of charge current-sense voltage. 1 = Sets charge current-sense voltage into overrange. 150.4mV (max) (3008mA x 50mA) sense voltage. | |

*Command: 0x14

ChargingCurrent() (POR: 0x0080)

The ChargingCurrent() command uses the write-word protocol (Figure 3a). The command code for ChargingCurrent() is 0x14 (0b00010100). The 16-bit binary number formed by D15–D0 represents the current-limit set point (I0) in milliamps. However, since the MAX1645B has 64mA resolution in setting I0, the D0–D5 bits are ignored as shown in Table 4. Figure 6 shows the mapping between I0 (the current-regulation-loop set point) and the ChargingCurrent() code. All codes above 0b00 1011 1100 0000 (3008mA) result in a current overrange, limiting the charger current to 3.008A. All codes below 0b0000 0000 1000 0000 (128mA) turn the charging current off. A 50m Ω sense resistor (R2 in Figure 1) is required to achieve the correct CODE/current scaling.

The power-on reset value for the ChargingCurrent() register is 0x0080; thus, the first time a MAX1645B is powered on, the BATT current regulates to 128mA. Any time

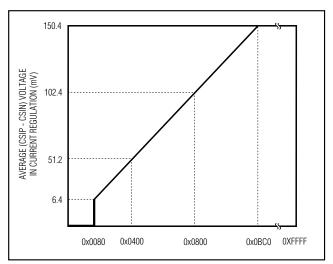


Figure 6. Average Voltage Between CSIP and CSIN vs. ChargingCurrent() Code

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Table 5. ChargingVoltage()*

| PIN | BIT NAME | FUNCTION | |
|-----|---------------------------|---|--|
| 0 | — | Not used. Normally a 1mV weight. | |
| 1 | | Not used. Normally a 2mV weight. | |
| 2 | — | Not used. Normally a 4mV weight. | |
| 3 | — | Not used. Normally an 8mV weight. | |
| 4 | Charge Voltage, DACV 0 | 0 = Adds 0mV of charger-voltage compliance. 1 = Adds 16mV of charger-voltage compliance, 1.024V (min). | |
| 5 | Charge Voltage, DACV 1 | 0 = Adds 0mV of charger-voltage compliance. 1 = Adds 32mV of charger-voltage compliance, 1.024V (min). | |
| 6 | Charge Voltage, DACV 2 | 0 = Adds 0mV of charger-voltage compliance. 1 = Adds 64mV of charger-voltage compliance, 1.024V (min). | |
| 7 | Charge Voltage, DACV 3 | 0 = Adds 0mV of charger-voltage compliance. 1 = Adds 128mV of charger-voltage compliance, 1.024V (min). | |
| 8 | Charge Voltage, DACV 4 | 0 = Adds 0mV of charger-voltage compliance. 1 = Adds 256mV of charger-voltage compliance, 1.024V (min). | |
| 9 | Charge Voltage, DACV 5 | 0 = Adds 0mV of charger-voltage compliance. 1 = Adds 512mV of charger-voltage compliance, 1.024V (min). | |
| 10 | Charge Voltage, DACV 6 | 0 = Adds 0mA of charger-voltage compliance. 1 = Adds 1024mV of charger-voltage compliance. | |
| 11 | Charge Voltage, DACV 7 | 0 = Adds 0mV of charger-voltage compliance. 1 = Adds 2048mV of charger-voltage compliance. | |
| 12 | Charge Voltage, DACV 8 | 0 = Adds 0mV of charger-voltage compliance. 1 = Adds 4096mV of charger-voltage compliance. | |
| 13 | Charge Voltage, DACV 9 | 0 = Adds 0mV of charger-voltage compliance. 1 = Adds 8192mV of charger-voltage compliance. | |
| 14 | Charge Voltage, DACV 10 | 0 = Adds 0mV of charger-voltage compliance. 1 = Adds 16384mV of charger-voltage compliance, 18432mV (max). | |
| 15 | Charge Voltage, Overrange | 0 = Adds 0mV of charger-voltage compliance. 1 = Sets charger compliance into overrange, 18432mV. | |

*Command: 0x15

the battery is removed, the ChargingCurrent() register returns to its power-on reset state.

ChargingVoltage() (POR: 0x4800)

The ChargingVoltage() command uses the write-word protocol (Figure 3a). The command code for ChargingVoltage() is 0x15 (0b00010101). The 16-bit binary number formed by D15–D0 represents the voltage set point (V0) in millivolts; however, since the

MAX1645B has 16mV resolution in setting V0, the D0, D1, D2, and D3 bits are ignored as shown in Table 5.

The ChargingVoltage() command is used to set the battery charging voltage compliance from 1.024V to 18.432V. All codes greater than or equal to 0b0100 1000 0000 0000 (18432mV) result in a voltage overrange, limiting the charger voltage to 18.432V. All codes below 0b0000 0100 0000 (1024mV) terminate charge. Figure 7 shows the mapping between V0





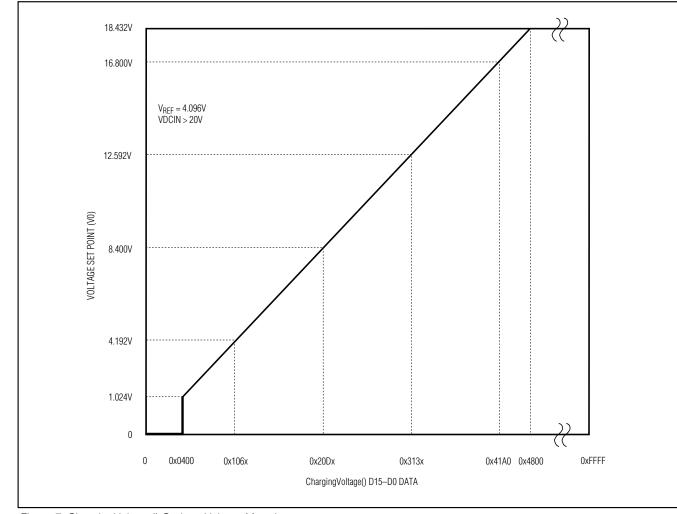


Figure 7. ChargingVoltage() Code to Voltage Mapping

(the voltage-regulation-loop set point) and the ChargingVoltage() code.

The power-on reset value for the ChargingVoltage() register is 0x4880; thus, the first time a MAX1645B is powered on, the BATT voltage regulates to 18.432V. Any time the battery is removed, the ChargingVoltage() register returns to its power-on reset state. The voltage at DAC corresponds to the set compliance voltage divided by 4.5.

AlarmWarning() (POR: Not Alarm)

The AlarmWarning() command uses the write-word protocol (Figure 3a). The command code for

AlarmWarning() is 0x16 (0b00010110). AlarmWarning() sets the ALARM_INHIBITED status bit in the MAX1645B if D15, D14, D13, D12, or D11 of the write-word protocol data equals 1. Table 6 summarizes the Alarm-Warning() command's function. The ALARM_INHIBITED status bit remains set until the battery is removed, a ChargerMode() command is written with the POR_RESET bit set, or new ChargingCurrent() AND ChargingVoltage() values are written. As long as ALARM_INHIBITED = 1, the MAX1645B switching regulators remain off.



Table 6. AlarmWarning()*

| BIT | BIT NAME | FUNCTION |
|-----|----------------------------|---|
| 0 | Error Code | Not used |
| 1 | Error Code | Not used |
| 2 | Error Code | Not used |
| 3 | Error Code | Not used |
| 4 | FULLY_DISCHARGED | Not used |
| 5 | FULLY_CHARGED | Not used |
| 6 | DISCHARGING | Not used |
| 7 | INITIALIZING | Not used |
| 8 | REMAINING_TIME_ ALARM | Not used |
| 9 | REMAINING_CAPACITY_ ALARM | Not used |
| 10 | Reserved | Not used |
| 11 | TERMINATE_ DISCHARGE_ALARM | 0 = Charge normally 1 = Terminate charging |
| 12 | OVER_TEMP_ALARM | 0 = Charge normally 1 = Terminate charging |
| 13 | OTHER_ALARM | 0 = Charge normally 1 = Terminate charging |
| 14 | TERMINATE_CHARGE_ ALARM | 0 = Charge normally 1 = Terminate charging |
| 15 | OVER_CHARGE_ALARM | 0 = Charge normally 1 = Terminate charging |

*Command: 0x16

Interrupts and Alert Response Address

The MAX1645B requests an interrupt by pulling the INT pin low. An interrupt is normally requested when there is a change in the state of the ChargerStatus() bits POWER_FAIL (bit 13), BATTERY_PRESENT (bit 14), or AC_PRESENT (bit 15). Therefore, the INT pin pulls low whenever the AC adapter is connected or disconnected, the battery is inserted or removed, or the charger goes in or out of dropout. The interrupts from each of the ChargerStatus() bits can be masked by an associated ChargerMode() bit POWER_FAIL_MASK (bit 6), BAT-TERY_PRESENT_MASK (bit 5), or AC_PRESENT_MASK (bit 4).

All interrupts are cleared by sending any command to the MAX1645B, or by sending a command to the AlertResponse() address, 0x19, using a modified receive-byte protocol. In this protocol, all devices that set an interrupt try to respond by transmitting their address, and the device with the highest priority, or most leading zeros, are recognized and cleared. The process repeats until all devices requesting interrupts are addressed and cleared. The MAX1645B responds to the AlertResponse() address with 0x13, which is its address and a trailing 1.

Charger Timeout

The MAX1645B includes a timer that terminates charge if the charger has not received a ChargingVoltage() or ChargingCurrent() command in 175s. During charging, the timer is reset each time a ChargingVoltage() or ChargingCurrent() command is received; this ensures that the charging cycle is not terminated.

If timeout occurs, charging terminates and both ChargingVoltage() and ChargingCurrent() commands are required to restart charging. A power-on reset also restarts charging at 128mA.

DC-to-DC Converter

The MAX1645B employs a buck regulator with a bootstrapped NMOS high-side switch and a low-side NMOS synchronous rectifier.

DC-to-DC Controller

The control scheme is a constant off-time, variable-frequency, cycle-by-cycle current mode. The off-time is constant for a given BATT voltage; it varies with V_{BATT} to keep the ripple current constant. During low-dropout operation, a maximum on-time of 10ms allows the controller to achieve >99% duty cycle with continuous conduction. Figure 8 shows the controller functional diagram.

MOSFET Drivers

The low-side driver output DLO swings from 0V to DLOV. DLOV is usually connected through a filter to LDO. The high-side driver output DHI is bootstrapped off LX and swings from V_{LX} to V_{BST}. When the low-side driver turns on, BST rises to one diode voltage below DLOV.

Filter DLOV with an RC circuit whose cutoff frequency is about 50kHz. The configuration in Figure 1 introduces a cutoff frequency of around 48kHz:

 $f = 1 / 2\pi RC = 1 / (2 \times \pi \times 33\Omega \times 0.1 \mu F) = 48 kHz$

Thermistor Comparators

Four thermistor comparators evaluate the voltage at the THM input to determine the battery temperature. This input is meant to be used with the internal thermistor connected to ground inside the battery pack. Connect the output of the battery thermistor to THM. Connect a resistor from THM to V_{DD} . The resistor-divider sets the voltage at THM. When the charger is not powered up, the battery temperature can still be determined if V_{DD} is powered from an external voltage source.

Thermistor Bits

Figure 9 shows the expected electrical behavior of a 103ETB-type thermistor (nominally 10k Ω at +25°C ±5% or better) to be used with the MAX1645B:

- THERMISTOR_OR bit is set when the thermistor value is >100kΩ. This indicates that the thermistor is open or a battery is not present. The charger is set to POR, and the BATTERY_PRESENT bit is cleared.
- THERMISTOR_COLD bit is set when the thermistor value is $>30k\Omega$. The thermistor indicates a cold battery. This bit does not affect the charge.
- THERMISTOR_HOT bit is set when the thermistor value is $<3k\Omega$. This is a latched bit and is cleared by removing the battery or sending a POR with the ChargerMode() command. The MAX1645B charger is stopped unless the HOT_STOP bit is cleared in the ChargerMode() command or the RES_UR bit is set. See Table 7.
- THERMISTOR_UR bit is set when the thermistor value is $<500\Omega$ (i.e., THM is grounded).

Multiple bits can be set depending on the value of the thermistor (e.g., a thermistor that is 450Ω causes both the THERMISTOR_HOT and the THERMISTOR_UR bits to be set). The thermistor can be replaced by fixed-value resistors in battery packs that do not require the thermistor as a secondary fail-safe indicator. In this case, it is the responsibility of the battery pack to manipulate the resistance to obtain correct charger behavior.



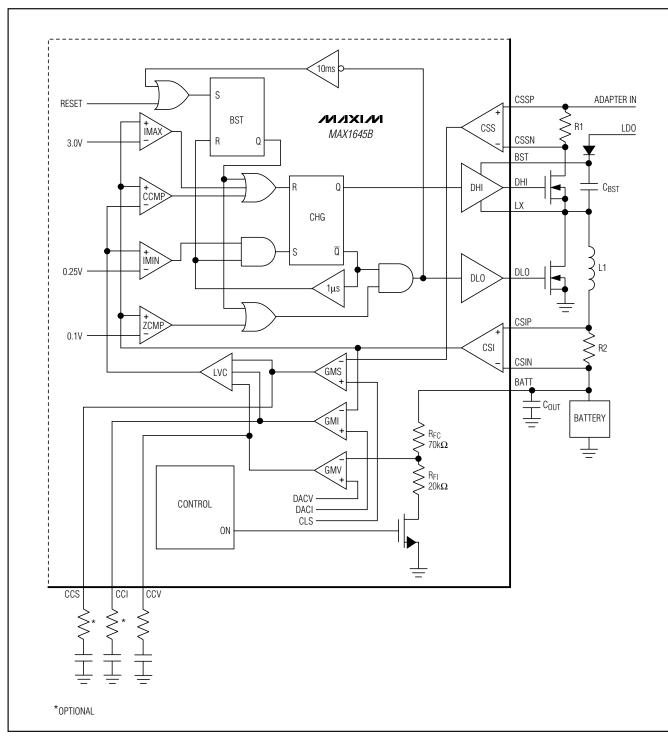


Figure 8. DC-to-DC Converter Functional Diagram

MAX1645B

Load and Source Switch Drivers

The MAX1645B can drive two P-channel MOSFETs to eliminate voltage drops across the Schottky diodes, which are normally used to switch the load current from the battery to the main DC source:

- The source switch P1 is controlled by PDS. This Pchannel MOSFET is turned on when CVS rises to 300mV above BATT and turns off when CVS falls to 100mV above BATT. The same signal that controls the PDS also sets the POWER_FAIL bit in the Charger Status() register. See Operating Conditions.
- Load switch P2 is controlled by PDL. This P-channel MOSFET is turned off when the CVS rises to 100mV below BATT and turns on when CVS falls to 300mV below BATT.

Dropout Operation

The MAX1645B has a 99.99% duty-cycle capability with a 10ms maximum on-time and 1µs off-time. This allows the charger to achieve dropout performance limited only by resistive losses in the DC-DC converter components (P1, R1, N1, R2; see Figure 1). The actual dropout voltage is limited to 300mV between CVS and BATT by the power-fail comparator (see *Operating Conditions*).

_Applications Information

Smart Battery Charging System/Background Information

A smart battery charging system, at a minimum, consists of a smart battery and smart battery charger compatible with the Smart Battery System Specifications using the SMBus.

A system can use one or more smart batteries. Figure 10 shows a single-battery system. This configuration is

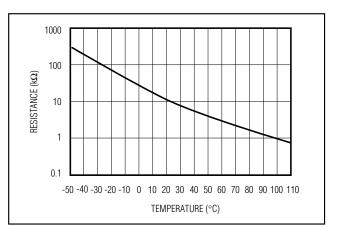


Figure 9. Typical Thermistor Characteristics

typically found in notebook computers, video cameras, cellular phones, or other portable electronic equipment.

Another configuration uses two or more smart batteries (Figure 11). The smart battery selector is used either to connect batteries to the smart battery charger or the system, or to disconnect them, as appropriate. For each battery, three connections must be made: power (the battery's positive and negative terminals), the SMBus (clock and data), and the safety signal (resistance, typically temperature dependent). Additionally, the system host must be able to query any battery so it can display the state of all batteries present in the system.

Figure 11 shows a two-battery system where battery 2 is being charged while battery 1 is powering the system. This configuration can be used to "condition" battery 1, allowing it to be fully discharged prior to recharge.

| THERMISTOR STATUS BIT | DESCRIPTION | WAKE-UP CHARGE | CONTROLLED CHARGE |
|--------------------------|-------------|----------------------------|----------------------|
| RES_UR and RES_HOT | Underrange | Allowed for timeout period | Allowed |
| RES_HOT | Hot | Not allowed | Not allowed |
| (None) | Normal | Allowed for timeout period | Allowed |
| RES_COLD | Cold | Allowed for timeout period | Allowed |
| RES_OR and RES_COLD | Overrange | Float charge* | Not allowed |

Table 7. Thermistor Bit Settings

*See Battery Present in the Operating Conditions section for more information.

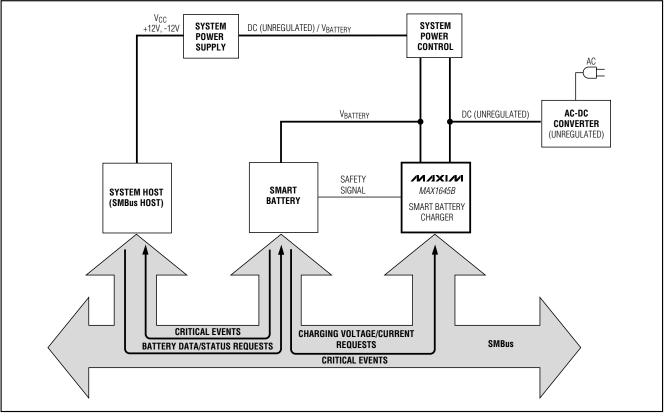


Figure 10. Typical Single Smart Battery System

Smart Battery Charger Types

Two types of smart battery chargers are defined: Level 2 and Level 3. All smart battery chargers communicate with the smart battery using the SMBus; the two types differ in their SMBus communication mode and whether they modify the charging algorithm of the smart battery (Table 8). Level 3 smart battery chargers are supersets of Level 2 chargers and, as such, support all Level 2 charger commands.

Level 2 Smart Battery Charger

The Level 2 or smart battery-controlled smart battery charger interprets the smart battery's critical warning messages and operates as an SMBus slave device to respond to the smart battery's ChargingVoltage() and ChargingCurrent() messages. The charger is obliged to adjust its output characteristics in direct response to the ChargingVoltage() and ChargingCurrent() messages it receives from the battery. In Level 2 charging, the smart battery is completely responsible for initiating the communication and providing the charging algorithm to the charger.

The smart battery is in the best position to tell the smart battery charger how it needs to be charged. The charging algorithm in the battery may request a static charge condition or may choose to periodically adjust the smart battery charger's output to meet its present needs. A Level 2 smart battery charger is truly chemistry independent and, since it is defined as an SMBus slave device only, the smart battery charger is relatively inexpensive and easy to implement.

Selecting External Components

Table 9 lists the suppliers' contacts; Table 10 lists the recommended components and refers to the circuit of Figure 1. The following sections describe how to select these components.

MOSFETs and Schottky Diodes

Schottky diode D1 provides power to the load when the AC adapter is inserted. Choose a 3A Schottky diode or higher. This diode may not be necessary if P1 is used. The P-channel MOSFET P1 turns on when V_{CVS} > V_{BATT}. This eliminates the voltage drop and power con-





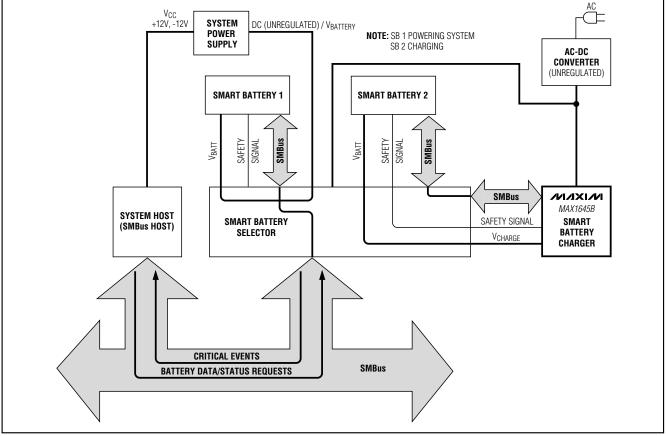


Figure 11. Typical System Using Multiple Smart Batteries

Table 8. Smart Battery Charger Typeby SMBus Mode and Charge AlgorithmSource

| | CHARGE ALGORITHM SOURCE | | |
|--------------|-------------------------|--------------------------|--|
| SMBus MODE | BATTERY | MODIFIED FROM BATTERY | |
| Slave only | Level 2 | Level 3 | |
| Slave/master | Level 3 | Level 3 | |

Note: Level 1 smart battery chargers were defined in the version 0.95a specification. While they can correctly interpret smart battery end-of-charge messages, minimizing overcharge, they do not provide truly chemistry-independent charging. They are no longer defined by the Smart Battery Charger Specification and are explicitly not compliant with this and subsequent smart battery charger specifications.

sumption of the Schottky diode. To minimize power loss, select a MOSFET with an R_{DS(ON)} of 50m Ω or less. This MOSFET must be able to deliver the maximum current as set by R1. D1 and P1 provide protection from reversed voltage at the adapter input.

N-channel MOSFETs N1 and N2 are the switching devices for the buck controller. High-side switch N1 should have a current rating of at least 6A and have an $R_{DS(ON)}$ of 50m Ω or less. The driver for N1 is powered by BST; its current should be less than 10mA. Select a MOSFET with a low total gate charge and determine the required drive current by IGATE = QGATE × f (where f is the DC-to-DC converter maximum switching frequency of 400kHz).

The low-side switch N2 should also have a current rating of at least 3A, have an $R_{DS(ON)}$ of $100m\Omega$ or less, and a total gate charge less than 10nC. N2 is used to provide the starting charge to the BST capacitor C14. During normal operation, the current is carried by Schottky diode D2. Choose a 3A or higher Schottky diode.



D3 is a signal-level diode, such as the 1N4148. This diode provides the supply current to the high-side MOSFET driver.

The P-channel MOSFET P2 delivers the current to the load when the AC adapter is removed. Select a MOSFET with an RDS(ON) of 50m Ω or less to minimize power loss and voltage drop.

Inductor Selection

Inductor L1 provides power to the battery while it is being charged. It must have a saturation current of at least 3A plus one-half of the current ripple (ΔI_L):

$$I_{SAT} = 3A + 1/2 \Delta I_L$$

The controller determines the constant off-time period, which is dependent on BATT voltage. This makes the ripple current independent of input and battery voltage and should be kept to less than 1A. Calculate the ΔI_L with the following equation:

$$\Delta I_L = 21 V \mu s / L$$

Higher inductor values decrease the ripple current. Smaller inductor values require higher saturation current capabilities and degrade efficiency. Typically, a 22µH inductor is ideal for all operating conditions.

| COMPONENT | MANUFACTURER | PART |
|----------------|--------------------------|---------------------------|
| | Sumida | CDRH127 series |
| Inductor | Coilcraft | D03316P series |
| | Coiltronics | UP2 series |
| | Internal Rectifier | IRF7309 |
| MOSFET | Fairchild | FDS series |
| | Vishay-Siliconix | Si4435/6 |
| Sense resistor | Dale | WSL series |
| Sense resistor | IRC | LR2010-01 series |
| Capacitor | AVX | TPS series, TAJ series |
| | Sprague | 595D series |
| | Motorola | 1N5817-1N5822 |
| Diode | Nihon | NSQ03A04 |
| DIOUE | Central Semiconductor | CMSH series |

Table 9. Component Suppliers

Other Components

CCV, CCI, and CCS are the compensation points for the three regulation loops. Bypass CCV with a 10k Ω resistor in series with a 0.01µF capacitor to GND. Bypass CCI and CCS with 0.01µF capacitors to GND. R7 and R13 serve as protection resistors to THM and CVS, respectively. To achieve acceptable accuracy, R6 should be 10k Ω and 1% to match the internal battery thermistor.

Current-Sense Input Filtering

In normal circuit operation with typical components, the current-sense signals can have high-frequency transients that exceed 0.5V due to large current changes and parasitic component inductance. To achieve proper battery and input current compliance, the current-sense input signals should be filtered to remove large common-mode transients. The input current-limit sensing circuitry is the most sensitive case due to large current steps in the input filter capacitors (C1 and C2) in Figure 1. Use 1 μ F ceramic capacitors from CSSP and CSSN to GND. Smaller 0.1 μ F ceramic capacitors can be used on the CSIP and CSIN inputs to GND since the current into the battery is continuous. Place these capacitors next to the single-point ground directly under the MAX1645B.

Layout and Bypassing

Bypass DCIN with a 1μ F to GND (Figure 1). D4 protects the device when the DC power source input is reversed. A signal diode for D4 is adequate as DCIN only powers the LDO and the internal reference. Bypass LDO, BST, DLOV, and other pins as shown in Figure 1.

Good PC board layout is required to achieve specified noise, efficiency, and stable performance. The PC board layout artist must be given explicit instructions, preferably a pencil sketch showing the placement of power-switching components and high-current routing. A ground plane is essential for optimum performance. In most applications, the circuit is located on a multilayer board, and full use of the four or more copper layers is recommended. Use the top layer for high-current connections, the bottom layer for quiet connections (REF, CCV, CCI, CCS, DAC, DCIN, VDD, and GND), and the inner layers for an uninterrupted ground plane.

Use the following step-by-step guide:

- 1) Place the high-power connections first, with their grounds adjacent:
 - Minimize current-sense resistor trace lengths and ensure accurate current sensing with Kelvin connections.

Table 10. Component Selection

MAX1645B

| DESIGNATION | DESCRIPTION | |
|----------------------------------|--|--|
| C1, C2 input capacitors | 22µF, 35V low-ESR tantalum capacitors AVX TPSE226M035R0300 | |
| C3, C4 output capacitors | 22µF, 25V low-ESR tantalum capacitors AVX TPSD226M025R0200 | |
| C5, C19, C20 | 1µF, >30V ceramic capacitors | |
| C6, C7, C12 | 1µF ceramic capacitors | |
| C8, C14, C16 | 0.1µF ceramic capacitors | |
| C9 compensation capacitor | 0.01µF ceramic capacitor | |
| C10, C11 compensation capacitors | 1nF ceramic capacitors | |
| C13 | 1500pF ceramic capacitor | |
| C18, C24 | 0.1µF, >20V ceramic capacitors | |
| C23 | 0.1µF, >30V ceramic capacitor | |
| D1, D2 | 40V, 2A Schottky diodes Central Semiconductor CMSH2-40 | |
| D3, D4 | Small-signal diodes Central Semiconductor CMPSH-3 | |
| L1 | 22µH, 3.6A buck inductor Sumida CDRH127-220 | |
| N1 high-side MOSFET | 30V, 11.5A, high-side N-channel MOSFET (8-pin SO) Fairchild FDS6680 30V, 8.4A, low-side N-channel MOSFET | |
| N2 low-side MOSFET | Fairchild FDS6612A or 30V, signal-level N-channel MOSFET 2N7002 | |
| P1, P2 | 30V, 11A P-channel MOSFETs load and source switches Fairchild FDS6675 | |
| R1 | $40m\Omega \pm 1\%$, 0.5W battery current-sense resistor Dale WSL-2010/40m\Omega/ $\pm 1\%$ | |
| R2 | $50m\Omega \pm 1\%$, 0.5W source current-sense resistor Dale WSL-2010/50m $\Omega/\pm 1\%$ | |
| R3, R4 | R3 + R4 >100k Ω input current-limit setting resistors | |
| R5, R7–R10, R17, R18 | $10k\Omega \pm 5\%$ resistors | |
| R6 | $10k\Omega \pm 1\%$ temperature sensor network resistor | |
| R11, R16 | $1\Omega \pm 5\%$ resistors | |
| R12 | $33\Omega \pm 5\%$ resistor | |
| R13 | $1 k\Omega \pm 5\%$ resistor | |
| R14, R15 | $4.7\Omega \pm 5\%$ resistors | |

Note: See Figure 1 for circuit configuration.

- Minimize ground trace lengths in the high-current paths.
- Minimize other trace lengths in the high-current paths:
 - Use >5mm-wide traces.
 - Connect C1 and C2 to high-side MOSFET (10mm (max) length).
 - Connect rectifier diode cathode to low-side MOSFET (5mm (max) length).
 - LX node (MOSFETs, rectifier cathode, inductor: 15mm (max) length). Ideally, surface-mount power components are flush against one another with their ground terminals almost touching. These high-current grounds are then connected to each other with a wide, filled zone of toplayer copper so they do not go through vias. The resulting top-layer subground plane is connected to the normal inner-layer ground plane at the output ground terminals, which ensures that the IC's analog ground is sensing at the supply's output terminals without interference from IR drops and ground noise. Other highcurrent paths should also be minimized, but focusing primarily on short ground and currentsense connections eliminates about 90% of all PC board layout problems.
- 2) Place the IC and signal components. Keep the main switching nodes (LX nodes) away from sensitive analog components (current-sense traces and REF capacitor). **Important:** The IC must be no further than 10mm from the current-sense resistors.

Keep the gate drive traces (DHI, DLO, and BST) shorter than 20mm and route them away from the current-sense lines and REF. Place ceramic bypass capacitors close to the IC. The bulk capacitors can be placed further away. Place the current-sense input filter capacitors under the part, connected directly to the GND pin.

3) Use a single-point star ground placed directly below the part. Connect the input ground trace, power ground (subground plane), and normal ground to this node.

Chip Information

TRANSISTOR COUNT: 6996

ADAPTER IN ≶ PDS CVS DCIN Ē CSSP \downarrow ΜΛΧΙΛΝ ≶ MAX1645B REF CSSN Ī LD0 $\overline{+}$ LOAD ≶ CLS BST GND DLOV DAC Ī CCV Ş DHI CCI LΧ CCS DLO PGND Ŧ CSIP CSIN PDL ٦E BATT Ş BATTERY ≶ $\overline{\Delta}$ THM HOST V_{DD} ≶ ≶ ≶ SCL SDA INT

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Typical Operating Circuit